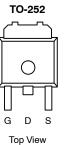


### SUD70N03-06P N-Channel 30 V (D-S) 175 ??C MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	r <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A) <sup>b</sup>		
30	0.006 @ V <sub>GS</sub> = 10 V	70		
	0.009 @ V <sub>GS</sub> = 4.5 V	70		



Drain Connected to Tab

Ordering Information: SUD70N03-06P

### **FEATURES**

- TrenchFET<sup>®</sup> Power MOSFET
- High Current
- 100% R<sub>g</sub> Tested

#### **APPLICATIONS**

- DC/DC Converters
  - Optimized For Low Side
- Synchronous Rectifiers

N-Channel MOSFET

D

Q

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = $25^{\circ}$ C UNLESS OTHERWISE NOTED)						
Parameter Drain-Source Voltage		Symbol	Limit	Unit		
		V <sub>DS</sub>	30			
Gate-Source Voltage		V <sub>GS</sub>	±20	V		
	$T_C = 25^{\circ}C$		70			
Continuous Drain Current <sup>a</sup>	$T_C = 100^{\circ}C$	ID ID	70 <sup>b</sup>			
Pulsed Drain Current		I <sub>DM</sub>	100	Α		
Continuous Source Current (Diode Conduction) <sup>a</sup>		IS	27			
Avalanche Current, single pulse		I <sub>AS</sub>	45			
Avalanche Energy, single pulse	L = 0.1 mH	E <sub>AS</sub>	101	mJ		
	$T_C = 25^{\circ}C$		88			
Maximum Power Dissipation	$T_A = 25^{\circ}C$	P <sub>D</sub>	8.3 <sup>a</sup>	W		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 175	°C		

G **O** 

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
	$t \le 10 \text{ sec}$	R <sub>thJA</sub>	15	18	°C/W	
Maximum Junction-to-Ambient <sup>a</sup>	Steady State		40	50		
Maximum Junction-to-Case		R <sub>thJC</sub>	1.4	1.7		

Notes

b. Limited by package.

Surface Mounted on FR4 Board, t  $\leq$  10 sec. a.



## SUD70N03-06P

N-Channel 30 V (D-S) 175 ??C MOSFET

Parameter	Symbol	Test Condition	Min	Typ <sup>a</sup>	Max	Unit	
Static					•	•	
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS}$ = 0 V, $I_D$ = 250 $\mu$ A	30				
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = 250 \ \mu A$	1.0		3.0	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS}$ = 0 V, $V_{GS}$ = ±20 V	$V, V_{GS} = \pm 20 V$		±100	nA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$			1	μΑ	
		$V_{DS}$ = 30 V, $V_{GS}$ = 0 V, $T_{J}$ = 125°C			50		
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 10 V	50			A	
		$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 20 \text{ A}$		0.0046	0.006	Ω	
Drain-Source On-State Resistance <sup>b</sup>	r <sub>DS(on)</sub>	$V_{GS}$ = 10 V, $I_{D}$ = 20 A, $T_{J}$ = 125°C			0.0105		
		$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 20 \text{ A}$		0.0072	0.009	1	
Forward Transconductanceb	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 20 A	20			S	
Dynamic <sup>a</sup>	- <b>I</b>					<b>I</b>	
Input Capacitance	C <sub>iss</sub>			3100			
Output Capacitance	C <sub>oss</sub>	$V_{GS}$ = 0 V, $V_{DS}$ = 25 V, f = 1 MHz	-	565		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	255			
Total Gate Charge <sup>c</sup>	Qg			21	30	nC	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS}$ = 15 V, $V_{GS}$ = 4.5 V, $I_{D}$ = 50 A		10			
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>		-	7.5			
Gate Resistance	Rg	f = 1 MHz	0.9	2.0	3.4	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			12	20	ns	
Rise Time <sup>c</sup>	tr	$V_{DD}$ = 15 V, R <sub>L</sub> = 0.3 $\Omega$		12	20		
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 50 \text{ A}, V_{\text{GEN}} = 10 \text{ V}, R_g = 2.5 \Omega$		30	45		
Fall Time <sup>c</sup>	t <sub>f</sub>			10	15		
Source-Drain Diode Ratings an	d Characteristi	c (T <sub>C</sub> = 25°C)				<b>I</b>	
Pulsed Current	I <sub>SM</sub>				100	A	
Diode Forward Voltage <sup>b</sup>	V <sub>SD</sub>	I <sub>F</sub> = 100 A, V <sub>GS</sub> = 0 V		1.2	1.5	V	
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 50 A, di/dt = 100 A/μs		35	70	ns	

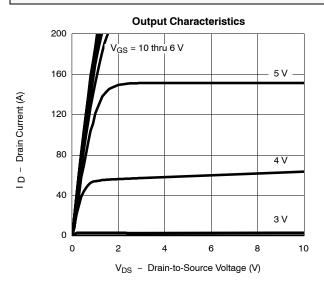
Notes

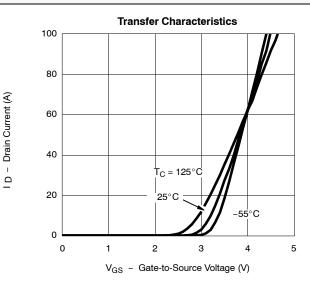
a. Guaranteed by design, not subject to production testing.

b. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2%.

c. Independent of operating temperature.

#### TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)





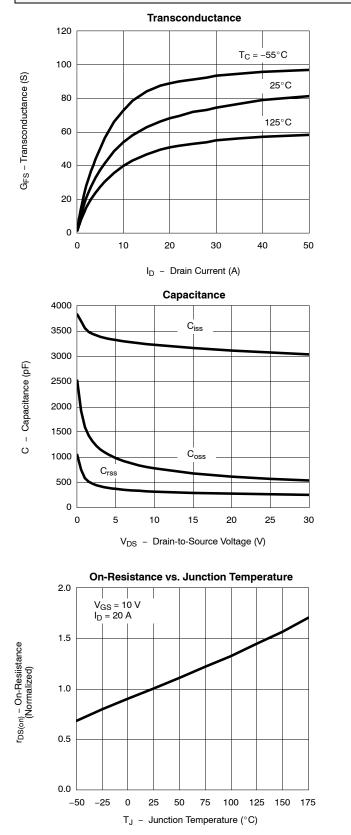


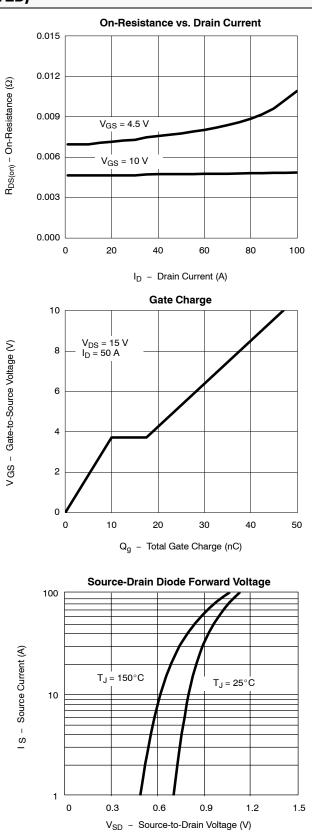
## SUD70N03-06P

N-Channel

30 V (D-S) 175 ??C MOSFET

#### TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



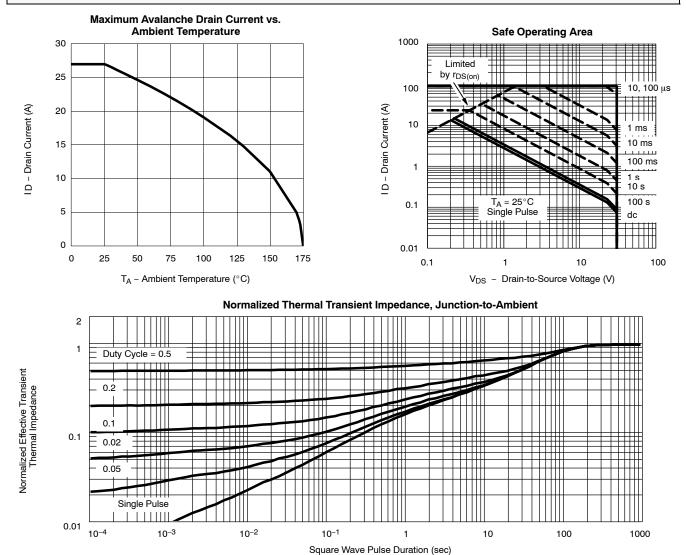


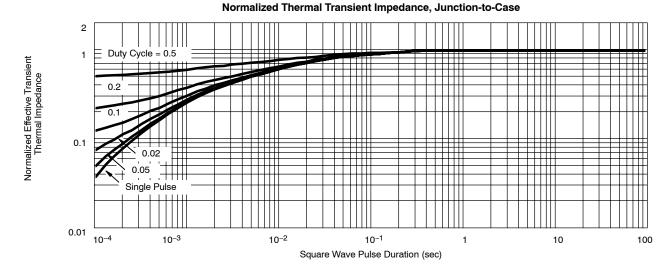


## SUD70N03-06P

N-Channel 30 V (D-S) 175 ??C MOSFET

#### THERMAL RATINGS







SUD70N03-06P N-Channel 30 V (D-S) 175 ??C MOSFET

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